

Amendments to the Claims

This listing of the Claims will replace all prior versions and listings of the claims in this patent application.

Listing of the Claims

1-14. (canceled)

15. (currently amended) A method for fabricating a semiconductor wafer with a patterned contact point comprising gold, comprising:

~~ion milling said patterned contact point for cleaning said patterned contact point,~~
wherein said cleaning said patterned contact point comprises ion milling.

Claim 16 (canceled)

17. (currently amended) The method of claim 15, wherein said ion milling ~~said patterned contact point~~ comprises using argon.

Claims 18-26. (canceled)

27. (currently amended) A method for fabricating a semiconductor wafer, comprising:

depositing a patterned metal bump on a topmost patterned circuit layer of said semiconductor wafer, wherein said patterned metal bump has a substantially flat top surface; and

~~ion milling said patterned metal bump for cleaning said~~ patterned metal bump,
wherein said cleaning said patterned metal bump comprises ion milling.

Claims 28 and 29. (canceled)

30. (currently amended) The method of claim 27, wherein said ion milling ~~said patterned metal bump~~ comprises using argon.

Claims 31-34. (canceled)